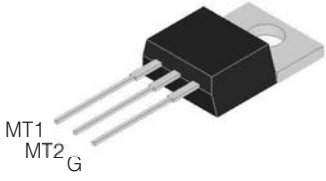
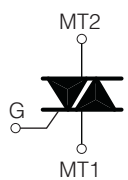


**INSULATED LOGIC LEVEL TRIAC**

<p style="text-align: center; font-weight: bold; font-size: 1.2em;">INSULATED TO-220AB</p> <div style="text-align: center; margin-top: 20px;">  </div> <div style="text-align: center; margin-top: 20px;">  </div>	<table style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%; text-align: center;"><b>On-State Current</b> 16 Amp</td> <td style="width: 50%; text-align: center;"><b>Gate Trigger Current</b> ≤ 10 mA (08)</td> </tr> <tr> <td colspan="2" style="text-align: center;"><b>Off-State Voltage</b> 200 V ÷ 800 V</td> </tr> </table> <p style="font-size: 0.9em; margin-top: 10px;">             * Logic Level current TRIAC              * Low thermal resistance with clip bounding              * Low thermal resistance isolation ceramic for FT....J         </p> <p style="font-size: 0.9em; margin-top: 10px;">             This series of TRIACs uses a high performance PNPN technology.         </p> <p style="font-size: 0.9em; margin-top: 10px;">             These parts are intended for general purpose AC switching applications with highly inductive loads. The FT....J series provides an isolated tab (rated at 2500 Vrms).         </p>	<b>On-State Current</b> 16 Amp	<b>Gate Trigger Current</b> ≤ 10 mA (08)	<b>Off-State Voltage</b> 200 V ÷ 800 V	
<b>On-State Current</b> 16 Amp	<b>Gate Trigger Current</b> ≤ 10 mA (08)				
<b>Off-State Voltage</b> 200 V ÷ 800 V					

**Absolute Maximum Ratings, according to IEC publication No. 134**

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	RMS On-state Current (full sine wave)	All Conduction Angle, $T_C = 83\text{ }^\circ\text{C}$	16	A
$I_{TSM}$	Non-repetitive On-State Current	Full Cycle, 60 Hz ( $t = 16.7\text{ ms}$ )	168	A
$I_{TSM}$	Non-repetitive On-State Current	Full Cycle, 50 Hz ( $t = 20\text{ ms}$ )	160	A
$I^2t$	Fusing Current	$t_p = 10\text{ ms}$ , Half Cycle	144	A <sup>2</sup> s
$I_{GM}$	Peak Gate Current	$20\text{ }\mu\text{s max.}$ $T_j = 125\text{ }^\circ\text{C}$	4	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125\text{ }^\circ\text{C}$	1	W
$di/dt$	Critical rate of rise of on-state current	$I_G = 2x I_{GT}$ , $t_r \leq 100\text{ ns}$ $f = 120\text{ Hz}$ , $T_j = 125\text{ }^\circ\text{C}$	50	A/ $\mu\text{s}$
$T_j$	Operating Temperature		(-40 + 125)	$^\circ\text{C}$
$T_{stg}$	Storage Temperature		(-40 + 150)	$^\circ\text{C}$
$T_{sld}$	Soldering Temperature	10s max	260	$^\circ\text{C}$

SYMBOL	PARAMETER	VOLTAGE				Unit
		B	D	M	N	
$V_{DRM} / V_{RRM}$	Repetitive Peak Off State Voltage	200	400	600	800	V

# INSULATED LOGIC LEVEL TRIAC

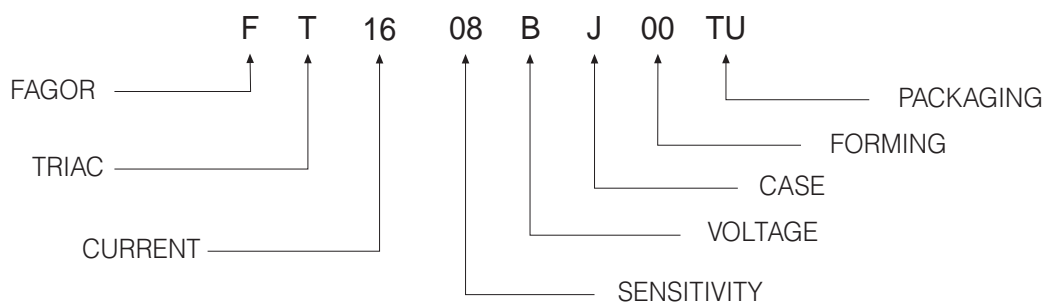
## Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY		Unit
						08	
I <sub>GT</sub> <sup>(1)</sup>	Gate Trigger Current	V <sub>D</sub> = 12 V <sub>DC</sub> , R <sub>L</sub> = 33Ω, T <sub>j</sub> = 25 °C	Q1÷Q3	MAX	10	mA	
			Q4	MAX	-	mA	
V <sub>GT</sub>	Gate Trigger Voltage	V <sub>D</sub> = 12 V <sub>DC</sub> , R <sub>L</sub> = 33Ω, T <sub>j</sub> = 25 °C	Q1÷Q3	MAX	1.3	V	
			Q1÷Q4	MAX	-	V	
V <sub>GD</sub>	Gate Non Trigger Voltage	V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> = 3.3 KΩ, T <sub>j</sub> = 125 °C	Q1÷Q3	MIN	0.2	V	
			Q1÷Q4	MIN	-	V	
I <sub>H</sub> <sup>(2)</sup>	Holding Current	I <sub>T</sub> = 100 mA, Gate open, T <sub>j</sub> = 25 °C		MAX	15	mA	
I <sub>L</sub>	Latching Current	I <sub>G</sub> = 1.2 I <sub>GT</sub> , T <sub>j</sub> = 25 °C	Q1,Q3	MAX	25	mA	
			Q2	MAX	30	mA	
dV/dt <sup>(2)</sup>	Critical Rate of Voltage Rise	V <sub>D</sub> = 0.67 x V <sub>DRM</sub> , Gate open T <sub>j</sub> = 125 °C		MIN	40	V/μs	
(dI/dt) <sub>c</sub> <sup>(2)</sup>	Critical Rate of Current Rise	(dv/dt) <sub>c</sub> = 0.1 V/μs T <sub>j</sub> = 125 °C (dv/dt) <sub>c</sub> = 10 V/μs T <sub>j</sub> = 125 °C		MIN	8.5	A/ms	
				MIN	3.0	A/ms	
V <sub>TM</sub> <sup>(2)</sup>	On-state Voltage	I <sub>T</sub> = 22.5 Amp, tp = 380 μs, T <sub>j</sub> = 25 °C		MAX	1.55	V	
V <sub>t(o)</sub> <sup>(2)</sup>	Threshold Voltage	T <sub>j</sub> = 125 °C		MAX	0.85	V	
r <sub>d</sub> <sup>(2)</sup>	Dynamic resistance	T <sub>j</sub> = 125 °C		MAX	25	mΩ	
I <sub>DRM</sub> /I <sub>RRM</sub>	Off-State Leakage Current	V <sub>D</sub> = V <sub>DRM</sub> , T <sub>j</sub> = 125 °C V <sub>R</sub> = V <sub>RRM</sub> , T <sub>j</sub> = 25 °C		MAX	2	mA	
				MAX	5	μA	
R <sub>th(j-c)</sub>	Thermal Resistance Junction-Case	for AC 360° conduction angle			2.1	°C/W	
R <sub>th(j-a)</sub>	Thermal Resistance Junction-Ambient	S = 1 cm <sup>2</sup>			60	°C/W	

(1) Minimum I<sub>GT</sub> is guaranteed at 5% of I<sub>GT</sub> max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

## PART NUMBER INFORMATION



**INSULATED LOGIC LEVEL TRIAC**

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

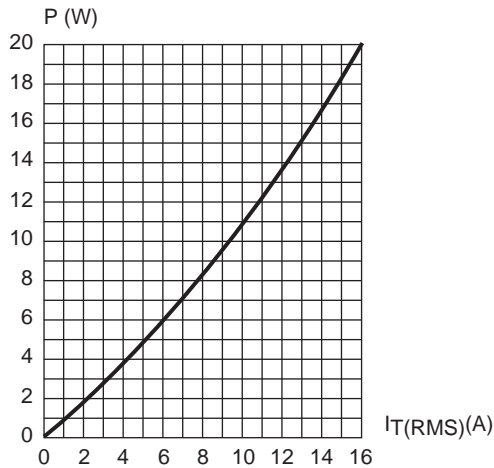


Fig. 2: RMS on-state current versus case temperature (full cycle).

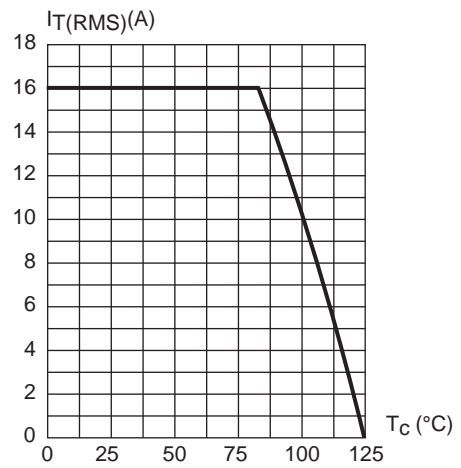


Fig. 3: Relative variation of thermal impedance versus pulse duration.

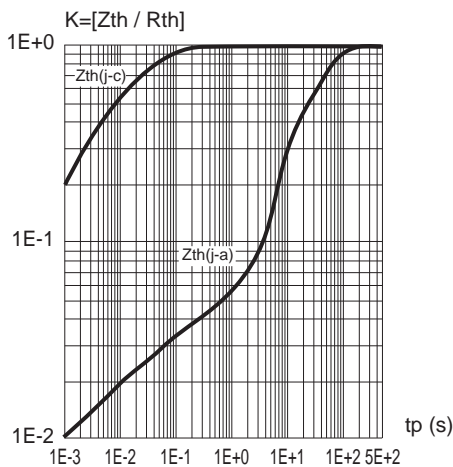


Fig. 4: On-state characteristics (maximum values)

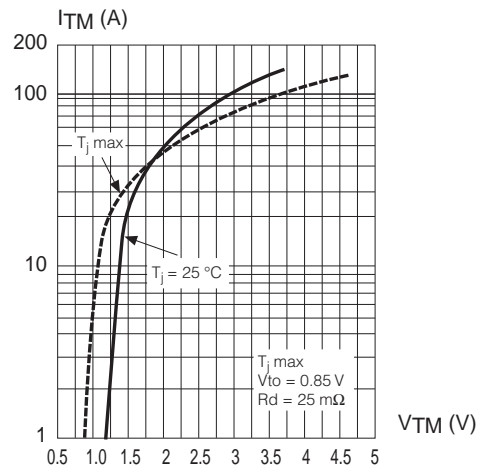


Fig. 5: Surge peak on-state current versus number of cycles

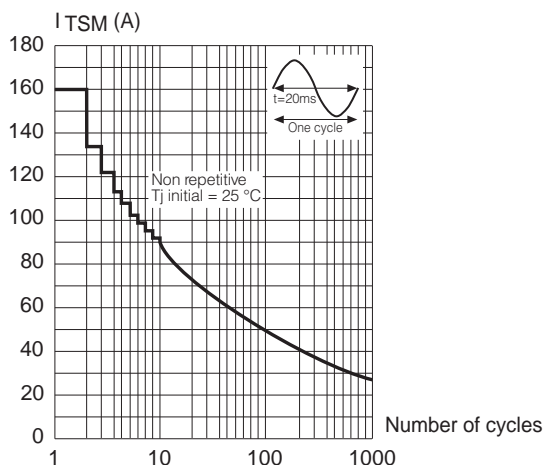
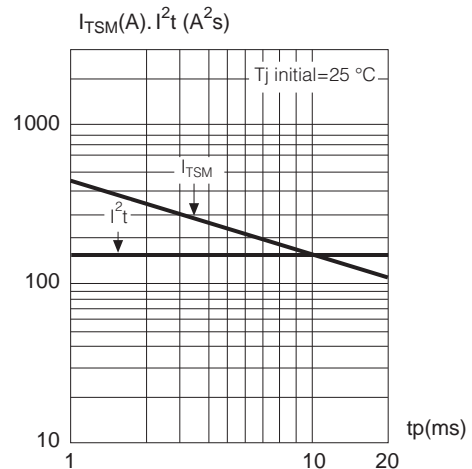


Fig. 6: Non repetitive surge peak on-state current for a sinusoidal pulse with width:  $t_p < 10$  ms, and corresponding value of  $I^2t$ .



**INSULATED LOGIC LEVEL TRIAC**

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

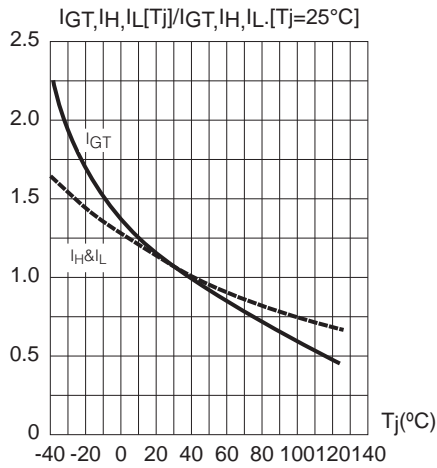


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature

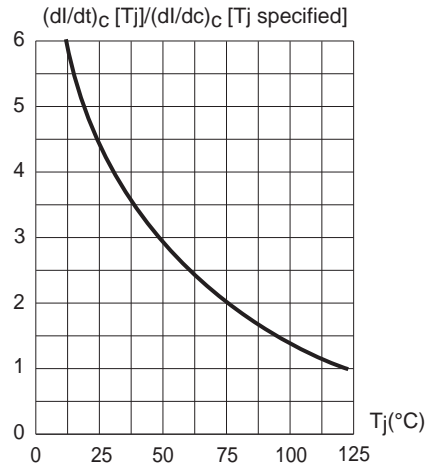
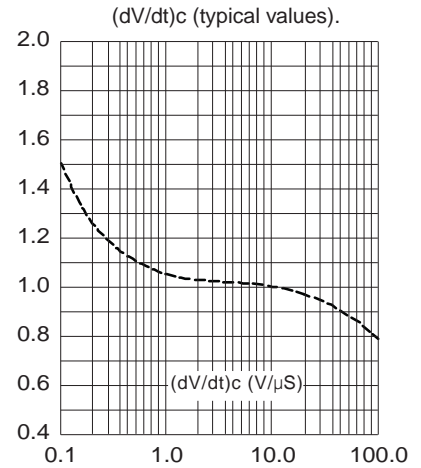


Fig. 9: Relative variation of critical rate of decrease of main current versus



**PACKAGE MECHANICAL DATA: INSULATED TO-220AB**

REF.	DIMENSIONS	
	Milimeters	
	Min.	Max.
A	3.56	4.83
A1	0.50	1.40
A2	2.00	2.92
b	0.38	1.02
b2	1.14	1.78
c	0.31	0.61
D	14.22	16.51
D1	8.38	9.02
E	9.65	10.67
e	2.49	2.59
e1	5.03	5.18
H1	5.84	6.86
L	12.70	14.74
L1		6.35
P	3.53	4.09
Q	2.54	3.43

**Mounting Torque**

**1 N.m**

(\*) Limiting values and life support applications, see Web page.